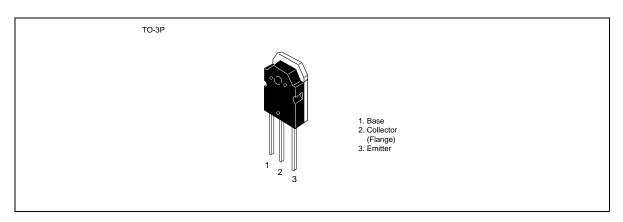
Silicon NPN Triple Diffused

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Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit V	
Collector to base voltage	V _{cbo}	150		
Collector to emitter voltage	V _{CEO} 80		V	
Emitter to base voltage	V _{ebo}	6	V	
Collector current	I _c	6	А	
Collector peak current	I _{C(peak)}	10	A W	
Collector power dissipation	P _c * ¹	50		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-50 to +150	°C	

Note: 1. Value at $T_c = 25^{\circ}C$.

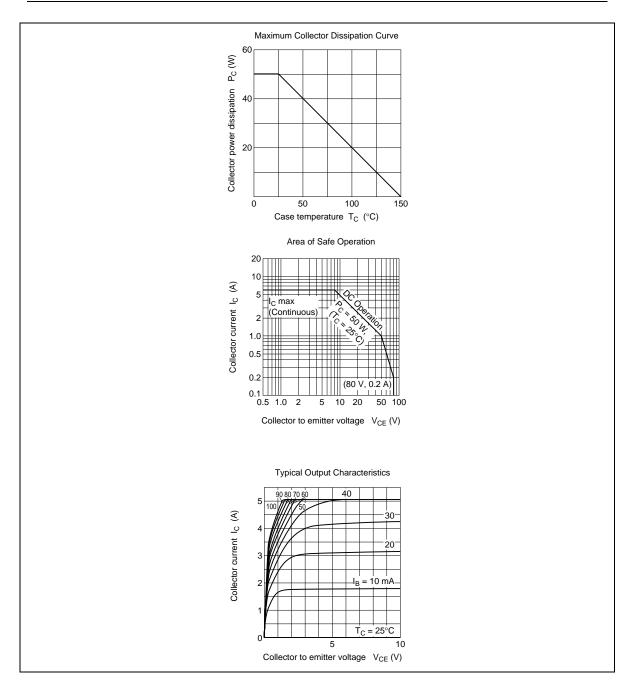
Electrical Characteristics (Ta = 25°C)

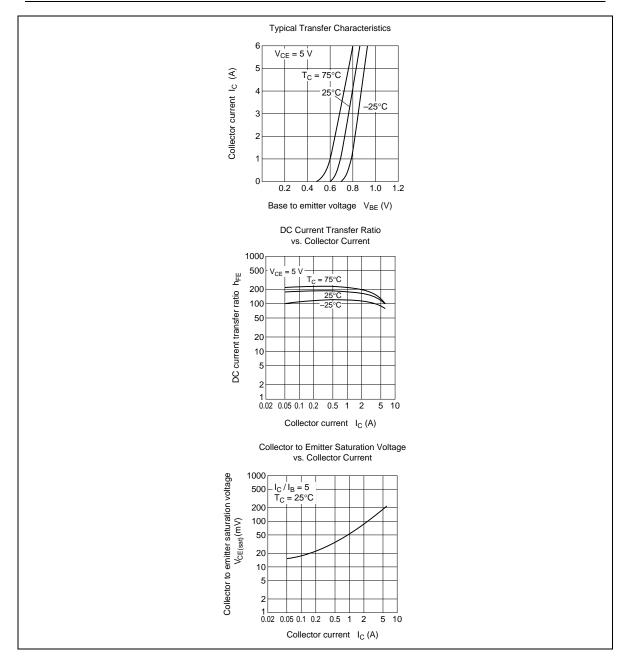
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	150	_	_	V	$I_{c} = 5 \text{ mA}, I_{e} = 0$
Collector to emitter breakdown voltage	$V_{\scriptscriptstyle (BR)CEO}$	80	_	_	V	$I_c = 50 \text{ mA}, \text{ R}_{_{\text{BE}}} = \infty$
Emitter to base breakdown voltage	$V_{\scriptscriptstyle (BR)EBO}$	6	_	_	V	$I_{e} = 5 \text{ mA}, I_{c} = 0$
Collector cutoff current	I _{cbo}	_		10	μA	$V_{_{CB}} = 120 \text{ V}, \text{ I}_{_{E}} = 0$
DC current transfer ratio	h_FE1 *1	60		200		$V_{ce} = 5 V, I_c = 1 A$
	$h_{_{FE2}}$	22			_	$V_{ce} = 5 V, I_c = 5 A$
Base to emitter voltage	V _{BE}	_		1.0	V	$V_{ce} = 5 V, I_c = 1 A$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_{c} = 5 \text{ A}, I_{B} = 1 \text{ A}$

Note: 1. The 2SD2342 is grouped by h_{FE1} as follows.

B C

60 to 120 100 to 200





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